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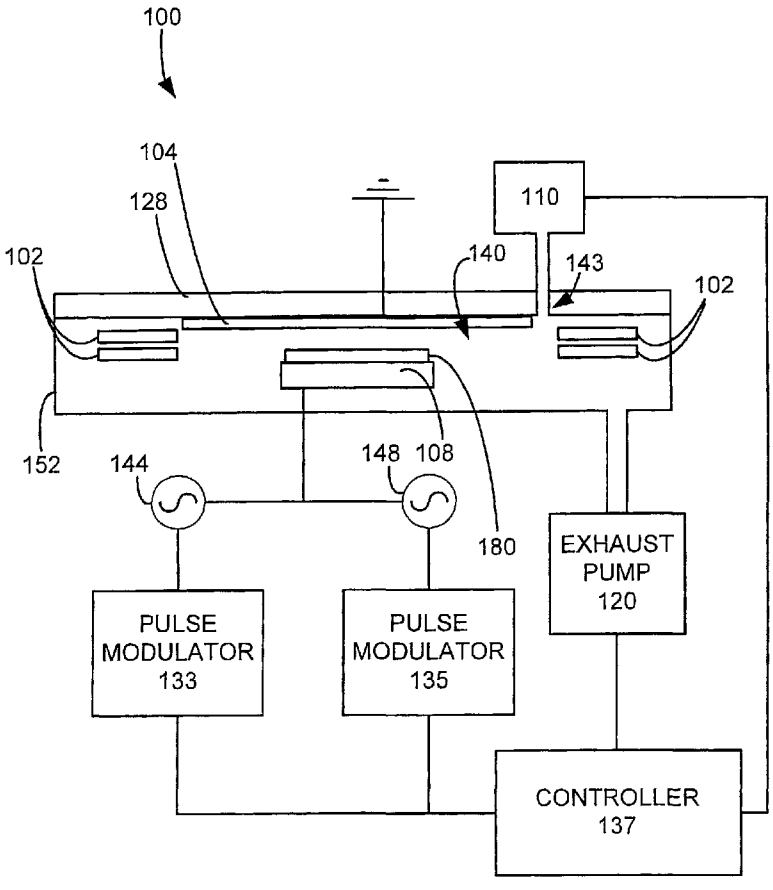
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(54) Title: RF PULSING OF A NARROW GAP CAPACITIVELY COUPLED REACTOR



(57) Abstract: An apparatus for providing a plasma etch of a layer over a wafer is provided, comprising a capacitively coupled process chamber (100), a gas source (110), a first (104) and a second electrode (108) within the process chamber. A first radio frequency power source (144) is electrically connected to at least one of the first and second electrodes, where the first radio frequency power source provides radio frequency power. A second radio frequency power source (148) is electrically connected to at least one of the first and second electrodes. A first modulation control (133) is connected to the first radio frequency power source, to provide a controlled modulation of the first radio frequency power source.

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